



## Description

The HIRL530NSPBF uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## General Features

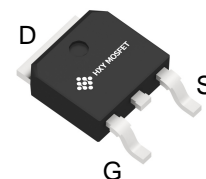
$V_{DS} = 100V, I_D = 15A$

$R_{DS(ON)} < 112m\Omega @ V_{GS} = 10V$

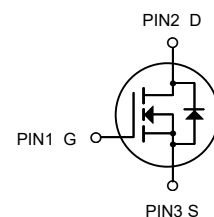
## Application

Power switch

DC/DC converters



TO-252-2L



N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HIRL530NSPBF	TO252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.7	A
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	3	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	2.4	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	24	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	6.1	mJ
$I_{AS}$	Avalanche Current	11	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation <sup>3</sup>	34.7	W
$P_D @ T_A = 25^\circ C$	Total Power Dissipation <sup>3</sup>	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	3.6	$^\circ C/W$



**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=250\mu A$	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1mA$	---	0.098	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V$ , $I_D=10A$	---	100	112	$m\Omega$
		$V_{GS}=4.5V$ , $I_D=8A$	---	117	130	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250\mu A$	1.0	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.57	---	$mV/^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=80V$ , $V_{GS}=0V$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=80V$ , $V_{GS}=0V$ , $T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V$ , $I_D=10A$	---	13	---	S
$R_g$	Gate Resistance	$V_{DS}=0V$ , $V_{GS}=0V$ , $f=1MHz$	---	2	---	$\Omega$
$Q_g$	Total Gate Charge (10V)	$V_{DS}=80V$ , $V_{GS}=10V$ , $I_D=10A$	---	26.2	---	nC
$Q_{gs}$	Gate-Source Charge		---	4.6	---	
$Q_{gd}$	Gate-Drain Charge		---	5.1	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V$ , $V_{GS}=10V$ , $R_G=3.3$ $I_D=10A$	---	4.2	---	ns
$T_r$	Rise Time		---	8.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	35.6	---	
$T_f$	Fall Time		---	9.6	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V$ , $V_{GS}=0V$ , $f=1MHz$	---	1535	---	pF
$C_{oss}$	Output Capacitance		---	60	---	
$C_{rss}$	Reverse Transfer Capacitance		---	37	---	
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V$ , Force Current	---	---	12	A
$I_{SM}$	Pulsed Source Current <sup>2,5</sup>		---	---	24	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V$ , $I_S=1A$ , $T_J=25^\circ\text{C}$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=10A$ , $dI/dt=100A/\mu s$ , $T_J=25^\circ\text{C}$	---	37	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	27.3	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=11A$
- 4.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 5 .The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



## Typical Characteristics

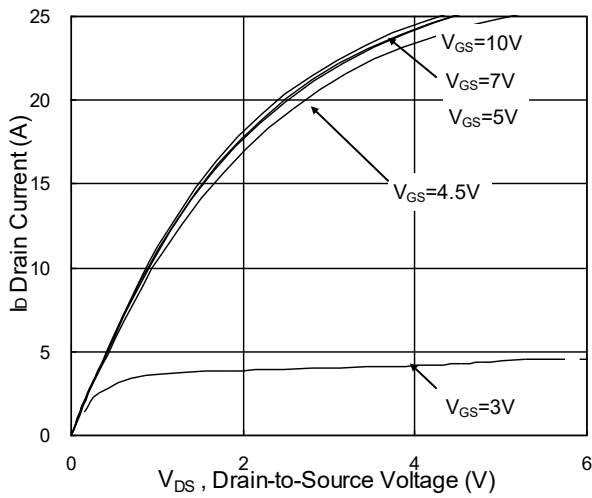


Fig.1 Typical Output Characteristics

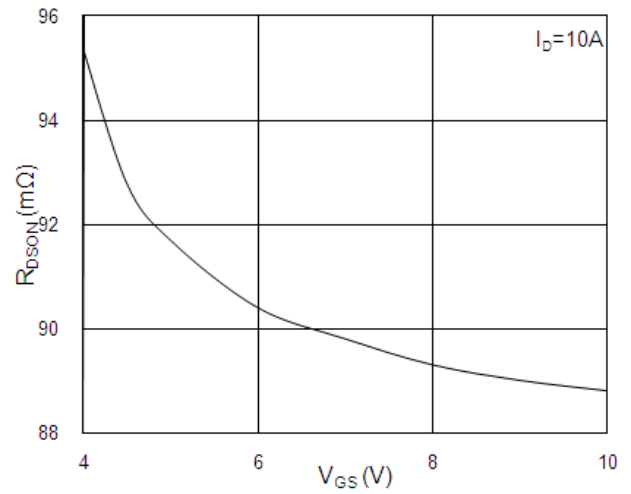


Fig.2 On-Resistance vs. Gate-Source

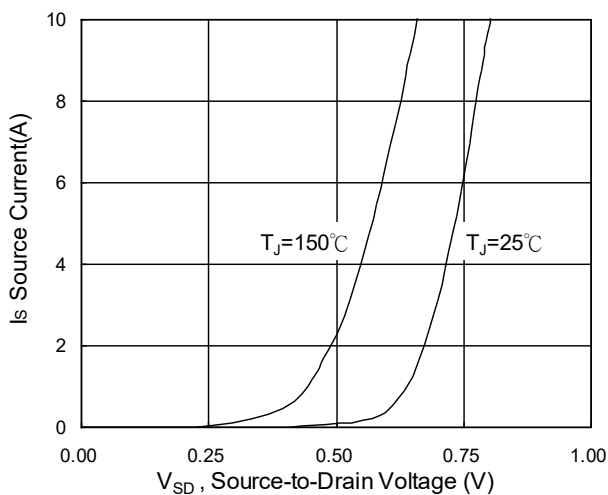


Fig.3 Forward Characteristics Of Reverse

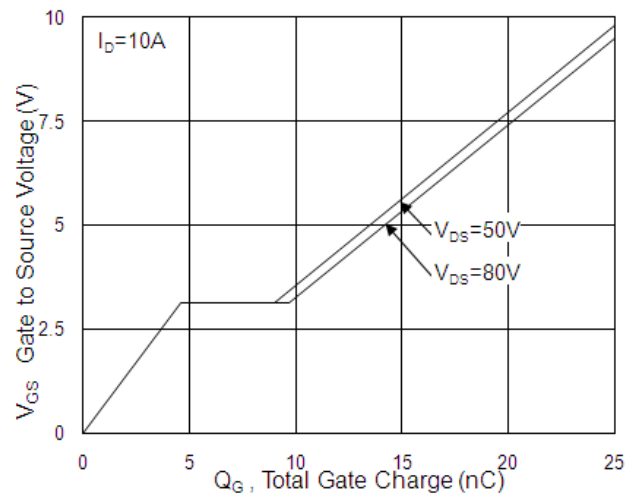


Fig.4 Gate-Charge Characteristics

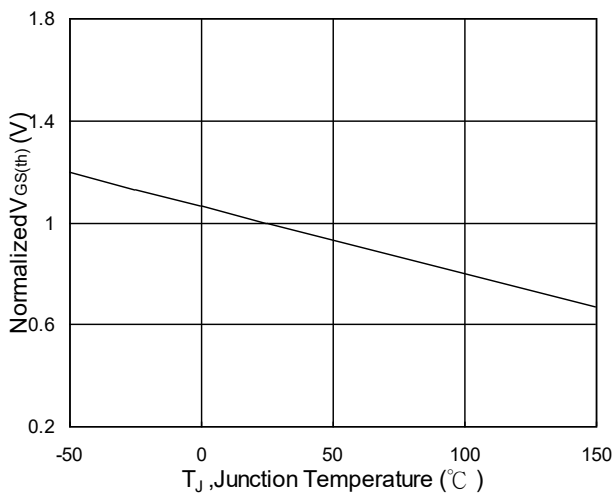


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

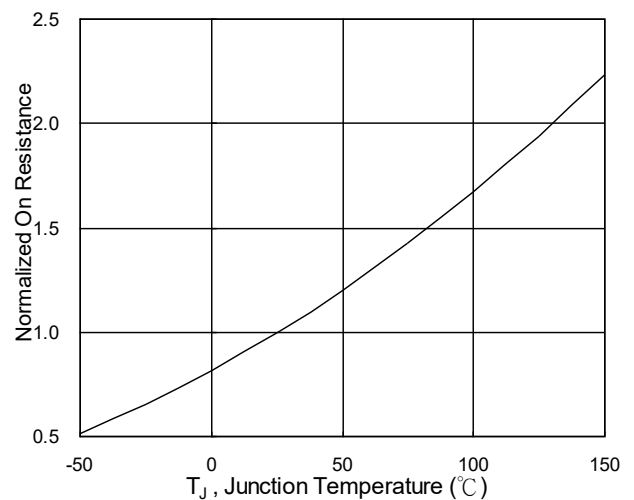


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

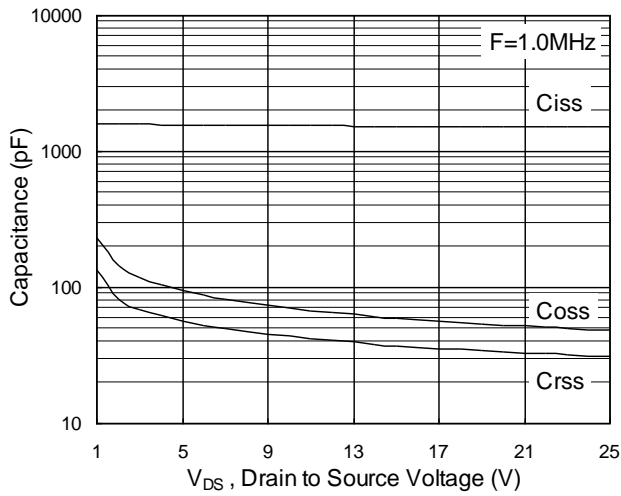


Fig.7 Capacitance

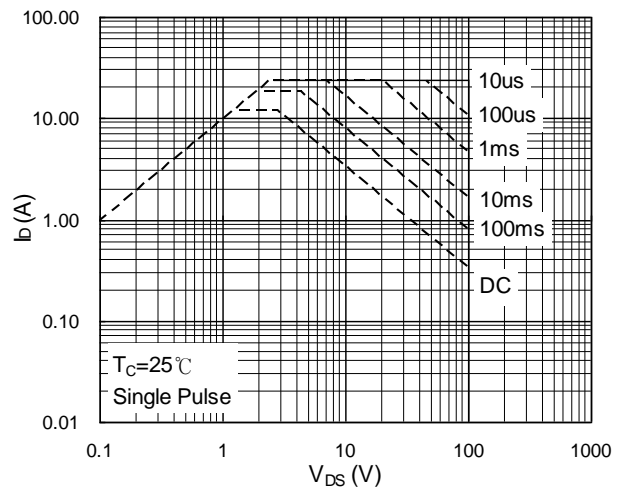


Fig.8 Safe Operating Area

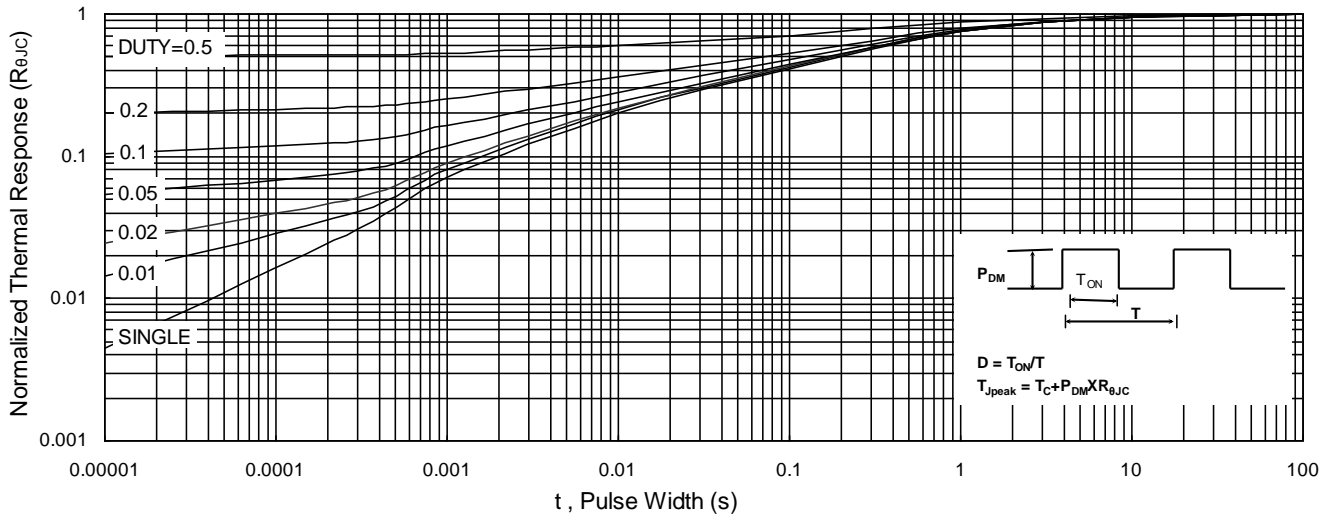


Fig.9 Normalized Maximum Transient Thermal Impedance

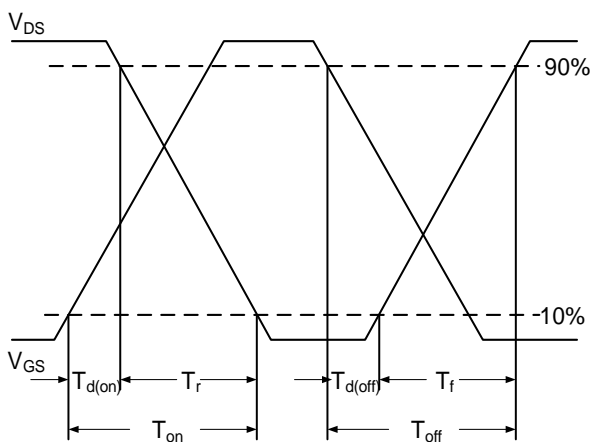


Fig.10 Switching Time Waveform

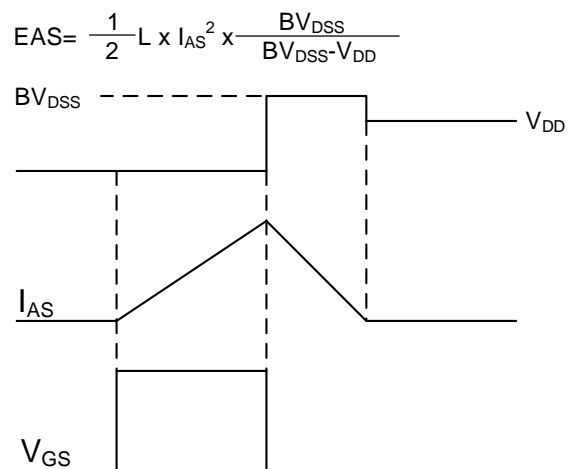
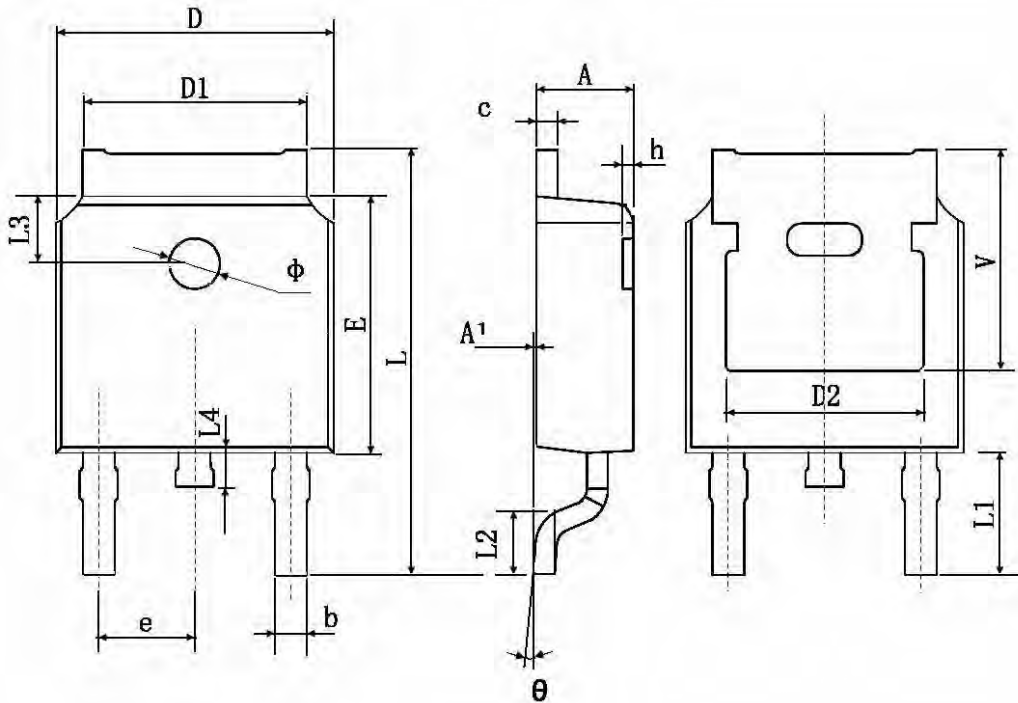


Fig.11 Unclamped Inductive Switching Waveform



## N-Channel Enhancement Mode MOSFET

## TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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